WHAT IS CLAIMED IS:

1	1. A lamellar diffraction grating comprising:
2	a substrate; and
3	an arrangement of generally rectangular protrusions spaced along the substrate
4	at an average grating period a , wherein an average height h and an average width w of the
5	protrusions is such that $h/a > 0.5$ and $w/a < 0.5$.
1	 The lamellar diffraction grating recited in claim 1 wherein the
2	generally rectangular protrusions have substantially equal heights and have substantially
3	equal widths.
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1	3. The lamellar diffraction grating recited in claim 1 wherein the grating
2	period corresponds to a line density $1/a$ between 700 and 1100 protrusions/mm.
1	4. The lamellar diffraction grating recited in claim 1 wherein the grating
	period corresponds to a line density 1/a between 800 and 1000 protrusions/mm.
2	period corresponds to a fine density the between 500 and 1500 productions.
1	5. The lamellar diffraction grating recited in claim 1 wherein h/a is
2	between 0.7 and 1.1 and wherein w/a is between 0.15 and 0.3.
1	6. The lamellar diffraction grating recited in claim 1 wherein h/a is
2	between 0.75 and 1.0 and wherein w/a is between 0.2 and 0.3.
	7. The lamellar diffraction grating recited in claim 1 wherein h/a is
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2	between 0.84 and 0.96 and wherein w/a is between 0.22 and 0.3.
1	8. The lamellar diffraction grating recited in claim 1 wherein the width of
2	each protrusion is defined by a FWHM measurement of a profile of such protrusion.
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1	A method for diffracting an optical signal, the method comprising:

- propagating the optical signal towards an arrangement of generally rectangular protrusions spaced along a substrate at an average grating period a, wherein an average height h and an average width w of the protrusions is such that h/a > 0.5 and w/a < 0.5; and reflecting the optical signal from the arrangement.
- 1 10. The method recited in claim 9 wherein each of the generally creating a rectangular protrusions has a substantially equal height and width.

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	11. The method recited in claim 9 wherein the grating period corresponds to a line density 1/a between 700 and 1100 protrusions/mm.
	12. The method recited in claim 9 wherein the grating period corresponds
;	to a line density $1/a$ between 800 and 1000 protrusions/mm.
	13. The method recited in claim 9 wherein h/a is between 0.7 and 1.1 and
:	wherein w/a is between 0.15 and 0.3.
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	14. The method recited in claim 9 wherein h/a is between 0.75 and 1.0 and
2	wherein w/a is between 0.2 and 0.3.
l	15. The method recited in claim 9 wherein h/a is between 0.84 and 0.96
2	and wherein w/a is between 0.22 and 0.3.
	16. The method recited in claim 9 wherein the width of each protrusion is
1 2	defined by a FWHM measurement of a profile of such protrusion.
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1	A lamellar diffraction grating comprising:
2	substrate means; and
3	means for reflecting an optical signal, such means for reflecting the optical
4	signal including an arrangement of generally rectangular protrusion means spaced along the
5	substrate means at an average grating period a , wherein an average height h and an average
6	width w of the protrusions is such that $h/a > 0.5$ and $w/a < 0.5$.
1	18. The lamellar diffraction grating recited in claim 17 wherein the grating
2	period corresponds to a line density 1/a between 800 and 1000 protrusions/mm.
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1	19. The lamellar diffraction grating recited in claim 17 wherein h/a is
2	between 0.84 and 0.96 and wherein w/a is between 0.22 and 0.3.
1	 A method for fabricating a lamellar diffraction grating, the method
2	comprising:

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substrate, the pattern having an average grating period a and defining an average protrusion

width w for the lamellar diffraction grating such that w/a < 0.5; and

forming a pattern for an anisotropic hard etch mask over a surface of a

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- etching a plurality of gaps into the substrate through the patterned anisotropic hard etch mask to an average depth h such that h/a > 0.5.
- The method recited in claim 20 wherein the grating period corresponds 21. 1 to a line density 1/a between 800 and 1000 protrusions/mm. 2
- The method recited in claim 20 wherein h/a is between 0.84 and 0.96 1 22 and wherein w/a is between 0.22 and 0.3. 2
 - The method recited in claim 20 wherein forming the pattern for the 23. anisotropic hard etch mask comprises:

depositing the anisotropic hard etch mask over the substrate;

forming a layer of photoresist over the anisotropic hard etch mask;

exposing the pattern onto the layer of photoresist;

etching the anisotropic hard etch mask through the pattern in the layer of photoresist; and

removing the layer of photoresist.

- The method recited in claim 23 wherein etching the anisotropic hard 24. etch mask comprises using isotropic reactive ion etching.
- The method recited in claim 23 wherein removing the layer of 25. photoresist comprises applying an organic solvent. 2
 - The method recited in claim 20 wherein etching the plurality of gaps 26. comprises performing an anisotropic chemical etch.
- A wavelength router for receiving, at an input port, light having a 27. 1 plurality of spectral bands and directing subsets of the spectral bands to respective ones of a 2 plurality of output ports, the wavelength router comprising a free-space optical train disposed 3 between the input port and the output ports providing optical paths for routing the spectral 4 bands, the optical train including a reflective lamellar diffraction grating disposed to intercept 5 light traveling from the input port, wherein the reflective lamellar diffraction grating has an 6 arrangement of generally rectangular protrusions spaced along a substrate at an average 7 grating period a, and an average height h and an average width w of the protrusions is such 8 that h/a > 0.5 and w/a < 0.5. 9

- 1 28. The wavelength router recited in claim 27 wherein the grating period corresponds to a line density 1/a between 800 and 1000 protrusions/mm.
- 1 29. The wavelength router recited in claim 27 wherein h/a is between 0.84
- 2 and 0.96 and wherein w/a is between 0.22 and 0.3.